

(19) United States

(12) Patent Application Publication (10) Pub. No.: US 2024/0237549 A1 Chiou et al.

Jul. 11, 2024 (43) **Pub. Date:**

(54) SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

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(21) Appl. No.: 18/610,212

(22) Filed: Mar. 19, 2024

Related U.S. Application Data

(63) Continuation of application No. 16/882,552, filed on May 25, 2020, now Pat. No. 11,968,906.

(30)Foreign Application Priority Data

Apr. 29, 2020 (CN) 202010354013.4

Publication Classification

(51)	Int. Cl.	
` ′	H10N 50/80	(2006.01)
	G11C 11/16	(2006.01)
	H01F 10/32	(2006.01)
	H01F 41/32	(2006.01)
	H10N 50/01	(2006.01)
	H10N 50/85	(2006.01)

(52) U.S. Cl. H10N 50/80 (2023.02); G11C 11/161 CPC (2013.01); H10N 50/01 (2023.02); H01F 10/3254 (2013.01); H01F 41/32 (2013.01); H10N 50/85 (2023.02)

(57)**ABSTRACT**

A method for fabricating a semiconductor device includes the steps of: forming a first inter-metal dielectric (IMD) layer on a substrate; forming a contact hole in the first IMD layer; forming a bottom electrode layer in the contact hole; forming a magnetic tunneling junction (MTJ) stack on the bottom electrode layer; and removing the MTJ stack and the bottom electrode layer to form a MTJ on a bottom electrode. Preferably, the bottom electrode protrudes above a top surface of the first IMD layer.

